

TO-92 Plastic-Encapsulate Transistors

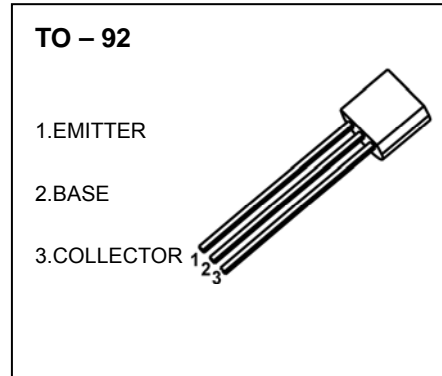
BC350 TRANSISTOR (PNP)

FEATURES

- General Purpose Switching and Amplification.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _C	Collector Power Dissipation	0.3	W
R _{θJA}	Thermal Resistance From Junction To Ambient	416	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-50V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-35V, I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-2mA	40		450	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-1mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=30MHz	125			MHz